

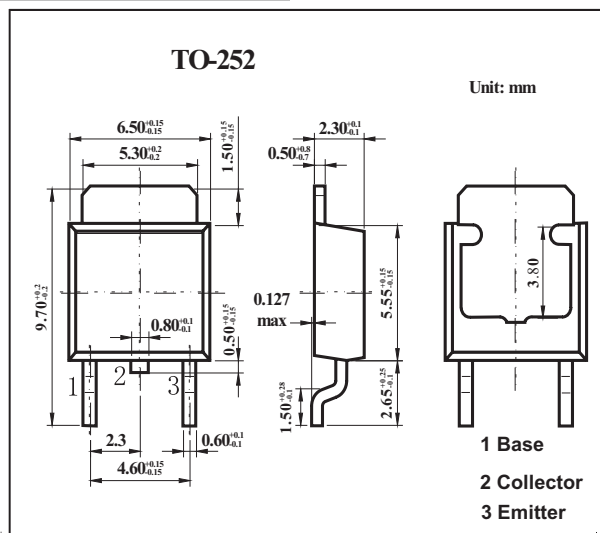
TO-252 Plastic-Encapsulate Transistors

FEATURES

- PNP TRANSISTORS
- Collector-Base Voltage: VCBO=-40V
- Low Speed Switching

MECHANICAL DATA

- Case style:TO-252 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-40	V
V _{CE0}	Collector-Emitter Voltage	-30	V
V _{EB0}	Emitter-Base Voltage	-6	V
I _c	Collector Current -Continuous	-3	A
P _C	Collector Power Dissipation	1.25	W
R _{eJA}	Thermal Resistance from Junction to Ambient	100	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

PACKAGE INFORMATION

Device	Package	Shipping
2SB772	TO-252	500/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V, I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} = -5V, I _C =-0.1A f =10MHZ	50	80		MHz

CLASSIFICATION OF h_{FE}

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400